

Kevin Jones

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104
papers

943
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17
h-index

27
g-index

106
ext. papers

1,025
ext. citations

3
avg, IF

3.61
L-index

#	Paper	IF	Citations
104	Nanostructured ion beam-modified Ge films for high capacity Li ion battery anodes. <i>Applied Physics Letters</i> , 2012 , 100, 083111	3.4	79
103	The effect of implant energy, dose, and dynamic annealing on end-of-range damage in Ge+-implanted silicon. <i>Journal of Applied Physics</i> , 1991 , 69, 2931-2937	2.5	66
102	Amorphization and graphitization of single-crystal diamond [A transmission electron microscopy study. <i>Diamond and Related Materials</i> , 2009 , 18, 1353-1359	3.5	62
101	Kinetics of solid phase epitaxial regrowth in amorphized Si _{0.88} Ge _{0.12} measured by time-resolved reflectivity. <i>Applied Physics Letters</i> , 1993 , 62, 501-503	3.4	44
100	Use of type II (end of range) damage as detectors for quantifying interstitial fluxes in ion-implanted silicon. <i>Journal of Applied Physics</i> , 1993 , 73, 4815-4819	2.5	44
99	Electrical and structural properties of In _x Ga _{1-x} N on GaAs. <i>Applied Physics Letters</i> , 1995 , 66, 1632-1634	3.4	39
98	Stressed multidirectional solid-phase epitaxial growth of Si. <i>Journal of Applied Physics</i> , 2009 , 105, 081101	2.5	36
97	Amorphization of elemental and compound semiconductors upon ion implantation. <i>Journal of Materials Research</i> , 1991 , 6, 1048-1054	2.5	33
96	Characterization of the gate oxide of an AlGa _N /Ga _N high electron mobility transistor. <i>Applied Physics Letters</i> , 2011 , 98, 122103	3.4	30
95	A study of point defect detectors created by Si and Ge implantation. <i>Journal of Applied Physics</i> , 1993 , 73, 955-960	2.5	27
94	Deposition, characterization and gas sensors application of RF magnetron-sputtered terbium-doped ZnO films. <i>Journal of Materials Science</i> , 2017 , 52, 8502-8517	4.3	25
93	Growth of In _x Ga _{1-x} N and In _x Al _{1-x} N on GaAs metalorganic molecular beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1995 , 13, 716-718	2.9	22
92	The effect of boron implant energy on transient enhanced diffusion in silicon. <i>Journal of Applied Physics</i> , 1997 , 81, 1656-1660	2.5	21
91	Characterization of Lanthanum Zirconate Formation at the A-Site-Deficient Strontium-Doped Lanthanum Manganite Cathode/Yttrium-Stabilized Zirconia Electrolyte Interface of Solid Oxide Fuel Cells. <i>Journal of the American Ceramic Society</i> , 2008 , 91, 2670-2675	3.8	20
90	Reverse gate bias-induced degradation of AlGa _N /Ga _N high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 1044-1047	1.3	19
89	Effect of uniaxial stress on solid phase epitaxy in patterned Si wafers. <i>Applied Physics Letters</i> , 2006 , 89, 082107	3.4	19
88	Modeling two-dimensional solid-phase epitaxial regrowth using level set methods. <i>Journal of Applied Physics</i> , 2009 , 105, 053701	2.5	18

87	Cycling performance and morphological evolution of pulsed laser-deposited FeF ₂ thin film cathodes for Li-ion batteries. <i>Journal of Materials Science</i> , 2015 , 50, 5174-5182	4.3	14
86	Surface processing with gas-cluster ions to improve giant magnetoresistance films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2001 , 19, 1207-1212	2.9	14
85	Dislocations in lattice-mismatched wide-gap II-VI/GaAs heterostructures as laser light scatterers: Experiment and theory. <i>Journal of Applied Physics</i> , 1995 , 78, 1203-1209	2.5	14
84	Maximizing electrical activation of ion-implanted Si in In _{0.53} Ga _{0.47} As. <i>Applied Physics Letters</i> , 2013 , 103, 232102	3.4	13
83	Dopant-stress synergy in Si solid-phase epitaxy. <i>Applied Physics Letters</i> , 2008 , 92, 232110	3.4	13
82	Effect of Fluorine on the Diffusion of Boron in Amorphous Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 717, 1		13
81	Strain Relief and Defect Formation in High Dose Oxygen Implanted Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 235, 103		13
80	Modulating the resistivity of MoS ₂ through low energy phosphorus plasma implantation. <i>Applied Physics Letters</i> , 2017 , 110, 262102	3.4	12
79	Effect of the end-of-range loop layer depth on the evolution of {311} defects. <i>Applied Physics Letters</i> , 1999 , 74, 700-702	3.4	12
78	GaAs/AlGaAs quantum well and modulation-doped heterostructures grown by organometallic vapor phase epitaxy using trimethylamine alane. <i>Applied Physics Letters</i> , 1991 , 59, 1975-1977	3.4	12
77	Substrate orientation dependence on the solid phase epitaxial growth rate of Ge. <i>Journal of Applied Physics</i> , 2013 , 113, 033505	2.5	11
76	Role of nucleation sites on the formation of nanoporous Ge. <i>Applied Physics Letters</i> , 2012 , 101, 131907	3.4	11
75	B segregation to grain boundaries and diffusion in polycrystalline Si with flash annealing. <i>Journal of Applied Physics</i> , 2012 , 111, 044508	2.5	11
74	Gas-cluster ion-beam smoothing of chemo-mechanical-polish processed GaSb(100) substrates. <i>Journal of Electronic Materials</i> , 2003 , 32, 842-848	1.9	10
73	Boron Solubility Limits Following Low Temperature Solid Phase Epitaxial Regrowth. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 669, 1		10
72	Effect of implant temperature on dopant diffusion and defect morphology for Si implanted GaAs. <i>Journal of Applied Physics</i> , 1994 , 76, 4571-4575	2.5	10
71	Field-induced defect morphology in Ni-gate AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2013 , 103, 023503	3.4	9
70	The effects of processing conditions on the density and microstructure of hot-pressed silicon powder. <i>Journal of Materials Science</i> , 1996 , 31, 4985-4990	4.3	9

69	Solid Phase Recrystallization and Strain Relaxation in Ion-Implanted Strained Si on SiGe Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 864, 4281		7
68	High-purity InP grown on Si by organometallic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1991 , 58, 1554-1556	3-4	7
67	The Effect of Implant Species on the Stability of Ion Implantation Damage. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 100, 277		7
66	Quantitative correlation of interfacial contamination and antiphase domain boundary density in GaAs on Si(100). <i>Journal of Materials Science</i> , 2016 , 51, 449-456	4-3	6
65	The effect of preamorphization energy on ultrashallow junction formation following ultrahigh-temperature annealing of ion-implanted silicon. <i>Journal of Applied Physics</i> , 2005 , 97, 044501	2-5	6
64	The Role of Vacancies and Interstitials in Transient Enhanced Diffusion of Arsenic Implanted into Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 469, 315		5
63	The effect of dose rate and implant temperature on transient enhanced diffusion in boron implanted silicon. <i>Journal of Electronic Materials</i> , 1997 , 26, 1361-1364	1-9	5
62	Effect of carbon codoping on boron diffusion in amorphous silicon. <i>Applied Physics Letters</i> , 2008 , 93, 072107	3-4	5
61	Epitaxial growth on gas cluster ion-beam processed GaSb substrates using molecular-beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004 , 22, 1455		5
60	Lateral Ge Diffusion During Oxidation of Si/SiGe Fins. <i>Nano Letters</i> , 2017 , 17, 2159-2164	11-5	4
59	Dissolution of antiphase domain boundaries in GaAs on Si(001) via post-growth annealing. <i>Journal of Materials Science</i> , 2019 , 54, 7028-7034	4-3	4
58	Junction Depth Reduction of ion Implanted Boron in Silicon Through Fluorine ion Implantation. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 610, 421		4
57	Capture of vacancies by extrinsic dislocation loops in silicon. <i>Applied Physics Letters</i> , 1998 , 72, 67-69	3-4	4
56	Sputtering Induced Changes in Defect Morphology and Dopant Diffusion for Si Implanted GaAs: Influence of Ion Energy and Implant Temperature. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 354, 337		4
55	Fermi-Level Effects on Extended Defect Evolution in Si ⁺ and P ⁺ Implanted In _{0.53} Ga _{0.47} As. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P3073-P3077	2	3
54	Activation and thermal stability of ultra-shallow B ⁺ -implants in Ge. <i>Journal of Applied Physics</i> , 2012 , 112, 123525	2-5	3
53	Effect of End-of-Range Defects, Arsenic Clustering and Precipitation on Transient Enhanced Diffusion in As ⁺ Implanted Si. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 469, 401		3
52	Boron diffusion in amorphous silicon-germanium alloys. <i>Applied Physics Letters</i> , 2008 , 92, 172108	3-4	3

51	Varying implant dose rate for defect reduction in laser thermal processing. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 339-343	4.3	3
50	The Effect of Impurities on Diffusion and Activation of ion Implanted Boron in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 610, 581		3
49	Interdiffusion Behavior of Si/Si _{1-x} Ge _x Layers in Inert and Oxidizing Ambients. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 532, 119		3
48	Effect of Extended Defects on the Enhanced Diffusion of Phosphorus Implanted Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 568, 199		3
47	Characterization of ZnS Layers Grown by MOCVD for Thin Film Electroluminescence (TFEL) Devices. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 242, 215		3
46	Use of a buried loop layer as a detector of interstitial flux during oxidation of SiGe heterostructures. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017 , 35, 021101	2.9	2
45	Wet-chemical etching of FIB lift-out TEM lamellae for damage-free analysis of 3-D nanostructures. <i>Ultramicroscopy</i> , 2020 , 216, 113049	3.1	2
44	Effect of Implant Energy on Silicon Defect Evolution. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 469, 283		2
43	Effect of low Ge content on B diffusion in amorphous SiGe alloys. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 333		2
42	Impact of the end of range damage from low energy Ge preamorphizing implants on the thermal stability of shallow boron profiles. <i>Journal of Applied Physics</i> , 2004 , 96, 4939-4944	2.5	2
41	Electrical and Structural Characterization of Boron Implanted Silicon Following Laser Thermal Processing. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 717, 1		2
40	Dose-rate effects in silicon-implanted gallium arsenide from low to high doses. <i>Journal of Electronic Materials</i> , 1996 , 25, 107-111	1.9	2
39	Correlation of Dislocation Loop Formation and Time Dependent Diffusion of Implanted P-Type Dopants in Gallium Arsenide. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 240, 715		2
38	Low-Energy Implantation of Si and Sn into GaAs. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 157, 677		2
37	Lattice kinetic Monte Carlo modeling of germanium solid phase epitaxial growth. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 93-96		1
36	Activation and defect dissolution of non-amorphizing, elevated temperature Si ⁺ implants into In _{0.53} Ga _{0.47} As 2014 ,		1
35	Deactivation of electrically supersaturated Te-doped InGaAs grown by MOCVD. <i>Journal of Materials Science</i> , 2017 , 52, 10879-10885	4.3	1
34	Phosphorus / Silicon Interstitial Annealing After Ion Implantation. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 610, 661		1

33	Effects of Co-Dopants on the Microstructure and El Properties of the ZnS:Mn Luminescence Materials. <i>Materials Research Society Symposia Proceedings</i> , 1999 , 560, 21		1
32	Blue And Yellow Light Emitting Phosphors For Thin Film Electroluminescent Displays. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 345, 289		1
31	Type II Dislocation Loops and their Effect on Strain in Ion Implanted Silicon as Studied by High Resolution X-ray Diffraction. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 378, 635		1
30	Point Defect Detector Studies of Oxidized Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 238, 101		1
29	Observation of the Wurtzite Phase in OMVPE Grown ZnSe/GaAs: Effect on Implantation and Rapid Thermal Annealing. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 339		1
28	The Defect Formation Mechanism Associated with Low Dose Implants into Si Fin Structures 2018 ,		1
27	Quantification of germanium-induced suppression of interstitial injection during oxidation of silicon. <i>Journal of Materials Science</i> , 2017 , 52, 10387-10392	4.3	0
26	Point Defect Detector Studies of Ge+ Implanted Silicon Upon Oxidation. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 262, 253		0
25	Defect evolution in ultralow energy, high dose helium implants of silicon performed at elevated temperatures. <i>Journal of Applied Physics</i> , 2018 , 124, 165708	2.5	0
24	The Role of Gallium Sulfide in Srs:Ce Grain Growth. <i>Microscopy and Microanalysis</i> , 1997 , 3, 987-988	0.5	
23	Using Quantitative TEM Analysis of Implant Damage to Study Surface Recombination Velocity in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 913, 1		
22	Concentration Dependence of Boron-Interstitial Cluster (BIC) Formation in Silicon-on-Insulator (SOI). <i>Materials Research Society Symposia Proceedings</i> , 2004 , 810, 357		
21	Reaction of Excess Silicon Interstitials in the Presence of Arsenic and Germanium. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 610, 841		
20	Influence of Arsenic Clustering and Precipitation on the Interstitial and Vacancy Concentration in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 669, 1		
19	Modeling of Dopant Defect Interactions. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 669, 1		
18	Effect of the End of Range Loop Layer Depth on the Evolution of {311} Defects. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 532, 61		
17	An Investigation of Vacancy Population During Arsenic Activation in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 442, 151		
16	Effect of Energy and Dose on Transient-Enhanced Diffusion and Defect Microstructure in Low Energy High Dose As+ Implanted Si. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 438, 21		

- 15 Effect of Energy and Dose on Transient-Enhanced Diffusion and Defect Microstructure in Low Energy High Dose As+ Implanted Si. *Materials Research Society Symposia Proceedings*, **1996**, 439, 29
- 14 Enhanced Dissolution of Extrinsic Dislocation Loops in Silicon Annealed in NH₃. *Materials Research Society Symposia Proceedings*, **1996**, 442, 157
- 13 Effect of Oxygen Dose Variation on the Simox Microstructure. *Materials Research Society Symposia Proceedings*, **1996**, 446, 207
- 12 The Effect of Titanium Silicidation on Type II End-of-Range Dislocation Loops. *Materials Research Society Symposia Proceedings*, **1994**, 337, 469
- 11 Thermal Expansion Behavior of ZnSe and ZnS_{0.03}Se_{0.97} Epilayers on GaAs at Temperatures in the Range, 25°C - 250°C. *Materials Research Society Symposia Proceedings*, **1994**, 340, 475
- 10 A Study of Loop Evolution During Inert Ambient Annealing and Reaction Between Point Defects and Dislocation Loops During Oxidation of Silicon. *Materials Research Society Symposia Proceedings*, **1994**, 354, 293
- 9 Carrier Confinement Effects in Epitaxial Silicon Quantum Wells Prepared by MOCVD. *Materials Research Society Symposia Proceedings*, **1994**, 358, 987
- 8 Effects of Arsenic Deactivation on Arsenic-Implant Induced Enhanced Diffusion in Silicon. *Materials Research Society Symposia Proceedings*, **1995**, 396, 167
- 7 Titanium Silicidation Induced Point Defects in Si. *Materials Research Society Symposia Proceedings*, **1995**, 402, 143
- 6 Solid Phase Epitaxial Regrowth of Implantation Amorphized Si_{0.7}Ge_{0.3} Grown on (100) Silicon. *Materials Research Society Symposia Proceedings*, **1991**, 235, 57
- 5 Time-Resolved Reflectivity Study of Solid-Phase Epitaxial Regrowth in Relaxed and Strained Si_{1-x}Ge_x Epilayers. *Materials Research Society Symposia Proceedings*, **1992**, 281, 479
- 4 The electron microscopy of post-growth induced defects of ZnSe/GaAs epilayers. *Journal of Electronic Materials*, **1993**, 22, 239-245 1.9
- 3 Raman Studies of Znse Lattice Damage and Recovery Due to N Implantation and Annealing. *Materials Research Society Symposia Proceedings*, **1990**, 209, 457
- 2 Ion Impiantation Doping of Si_{ox} with ³¹P and ⁶⁹Ga. *Materials Research Society Symposia Proceedings*, **1988**, 128, 617
- 1 A new planar defect in SiGe nanopillars. *Microscopy and Microanalysis*, **2021**, 27, 1948-1949 0.5